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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$	0.0045
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.0055
I _D (A)	60
Configuration	Single

PowerPAK® SO-8L Single

FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^c
- 100 % Rq and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ886EP-T1-GE3

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (7)	$\Gamma_{\rm C}$ = 25 °C, unles	s otherwise noted			
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V_{DS}	40	V		
Gate-Source Voltage	V_{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	1	60		
Continuous Drain Current	T _C = 125 °C	I _D	45		
Continuous Source Current (Diode Conduction)	I _S	50	А		
Pulsed Drain Current ^a		I _{DM}	240		
Single Pulse Avalanche Current	ent		36		
ingle Pulse Avalanche Energy		E _{AS}	64	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D	55	W	
	T _C = 125 °C	P _D	18		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	00	
Soldering Recommendations (Peak Temperature) ^{d, e}		-	260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	70	°C/W
Junction-to-Case (Drain)		R_{thJC}	2.7	C/VV

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	40	-	-	.,
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 15.3 A	-	0.0036	0.0045	
Drain-Source On-State Resistance ^a	В	V _{GS} = 4.5 V	I _D = 13.8 A	-	0.0045	0.0055	Ω
Drain-Source On-State Resistance ⁴	R _{DS(on)}	V _{GS} = 10 V	I _D = 15.3 A, T _J = 125 °C	-	-	0.0072	Ω
		V _{GS} = 10 V	I _D = 15.3 A, T _J = 175 °C	-	-	0.0088	1
Forward Transconductanceb	9 _{fs}	V _{DS} =	= 15 V, I _D = 15.3 A	-	105	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2338	2922	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 20 \text{ V, f} = 1 \text{ MHz}$	-	356	445	pF
Reverse Transfer Capacitance	C _{rss}			-	147	184	
Total Gate Charge ^c	Qg			-	43	65	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_{D} = 20 \text{ A}$	-	8	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	7	-	
Gate Resistance	R _g		f = 1 MHz	1.25	2.45	5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	8	12	
Rise Time ^c	t _r	V _{DD}	= 20 V, $R_1 = 2 \Omega$	-	17	25	
Turn-Off Delay Time ^c	t _{d(off)}		$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	29	44	ns
Fall Time ^c	t _f	1		-	6	9	
Source-Drain Diode Ratings and Chara	acteristics ^b	•			•		
Pulsed Current ^a	I _{SM}			-	-	240	Α
Forward Voltage	V_{SD}	le =	10.1 A, V _{GS} = 0	-	0.8	1.2	V

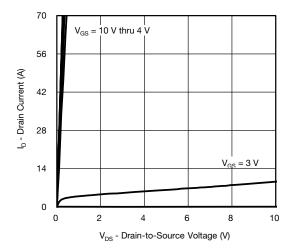
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

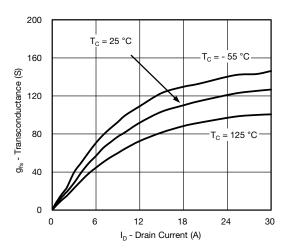
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



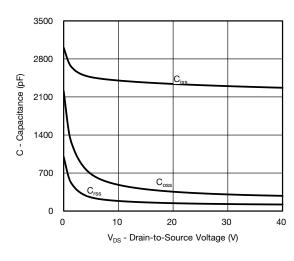
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



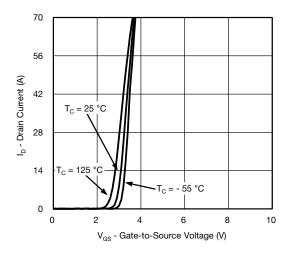
Output Characteristics



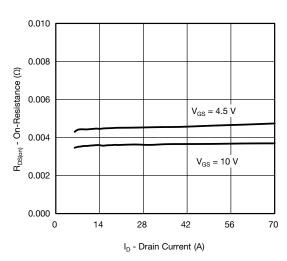
Transconductance



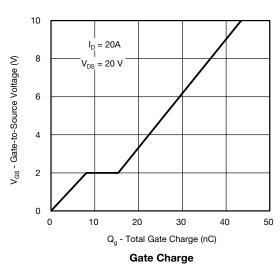
Capacitance



Transfer Characteristics

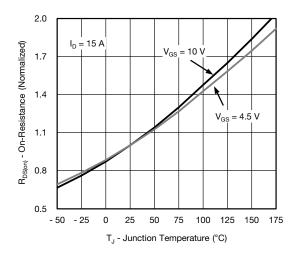


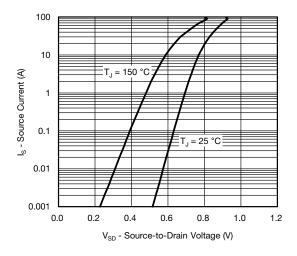
On-Resistance vs. Drain Current



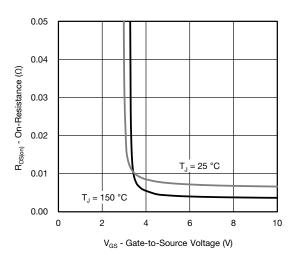


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

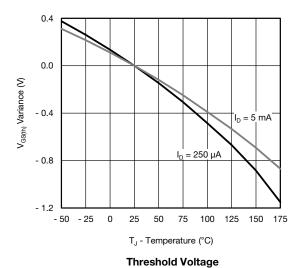




On-Resistance vs. Junction Temperature

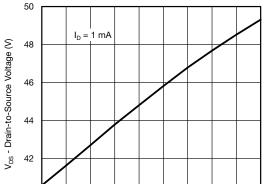


Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

40 - 50 - 25 0 25 50 75 100 125

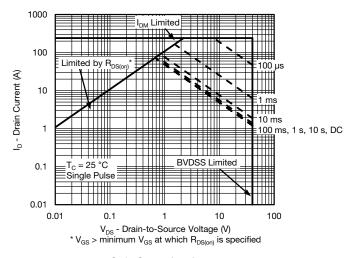


T_J - Junction Temperature (°C) Drain Source Breakdown vs. Junction Temperature

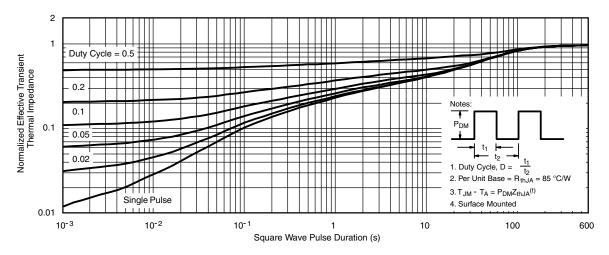
150 175



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



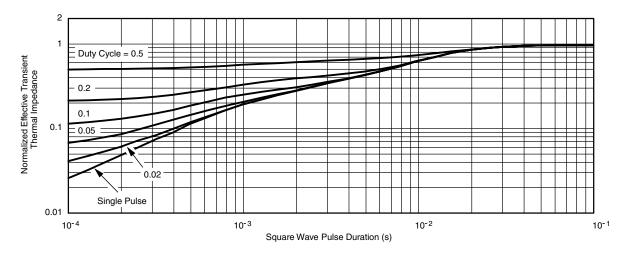
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

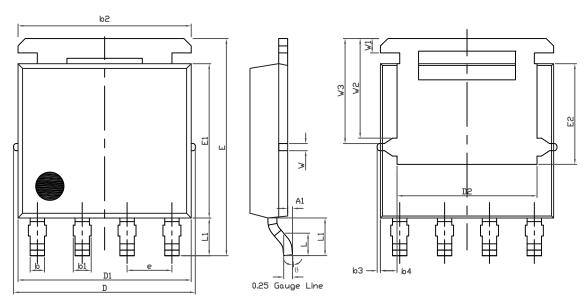
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

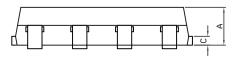
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262790.

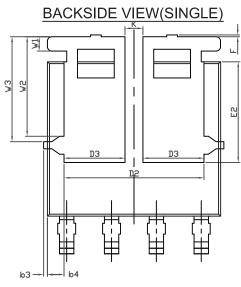


PowerPAK® SO-8L Case Outline 2



TOPSIDE VIEW





BACKSIDE VIEW(DUAL)



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DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.		
Α	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094			0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC		0.050 BSC				
Е	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
K		0.51			0.020			
W		0.23		0.009				
W1		0.41		0.016				
W2	2.82		0.111					
W3		2.96			0.117			
q	0°	-	10°	0°	-	10°		

ECN: S19-0643-Rev. B, 05-Aug-2019

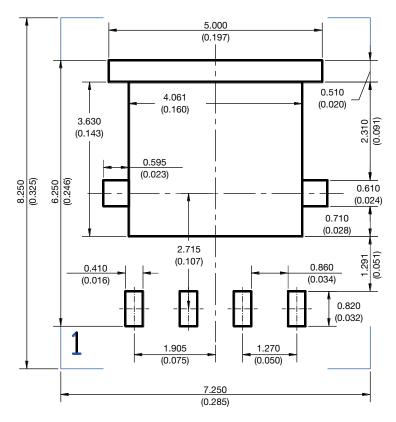
DWG: 6044

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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